

PNP SILICON EPITAXIAL TRANSISTOR

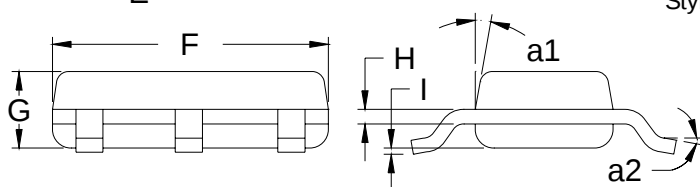
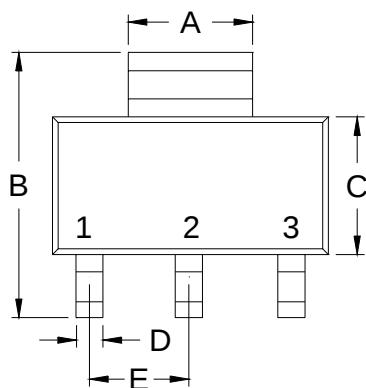
Features:

- Collector-Emitter Voltage: $V_{CEO} = -80V$
- Complementary to KLBCP56

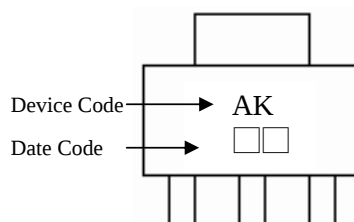
Description:

The KLBCX53 is designed for use in driver stages of audio amplifiers and medium power general purpose amplification.

SOT-223 Dimension



Marking:



Style: Pin 1.Base 2.Collector 3.Emitter

3-Lead SOT-223 Plastic
 Surface Mounted Package
 Code: L3

*: Typical

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.1142	0.1220	2.90	3.10	G	0.0551	0.0709	1.40	1.80
B	0.2638	0.2874	6.70	7.30	H	0.0098	0.0138	0.25	0.35
C	0.1299	0.1457	3.30	3.70	I	0.0008	0.0039	0.02	0.10
D	0.0236	0.0315	0.60	0.80	a1	*13°	-	*13°	-
E	*0.090	-	*2.3	-	a2	0°	10°	0°	10°
F	0.2480	0.2638	6.30	6.70					

Absolute Maximum Ratings at $T_a = 25^{\circ}C$

Parameter	Symbol	Ratings	Unit
Junction Temperature	T_j	+150	$^{\circ}C$
Storage Temperature Range	T_{STG}	-65 ~ +150	$^{\circ}C$
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collect Current(DC)	I_C	1	A
Total Power Dissipation	P_D	1.5	W

Electrical Characteristics (Ta = 25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-100	-	-	V	IC=-100uA, IE=0
BVCEO	-80	-	-	V	IC=-1mA, IB=0
BVEBO	-5	-	-	V	IE=-10uA, IC=0
ICBO	-	-	-100	nA	VCB=-30V, IE=0
IEBO	-	-	-100	nA	VEB=-5V, IC=0
*VCE(sat)1	-	-	-500	mV	IC=-500mA, IB=-50mA
*VBE(on)	-	-	-1000	mV	IC=-500mA, VCE=-2V,
*hFE1	63	-	-		VCE=-2V, IC=-5mA
*hFE2	63	-	250		VCE=-2V, IC=-150mA
*hFE3	40	-	-		VCE=-2V, IC=-500mA
fT	100	-	-	MHz	VCE=-5V, IC=-10mA, f=100MHz

* Pulse Test: Pulse Width≤380 s, Duty Cycle≤2%

Classification Of hFE2

Rank	A	B
Range	63 - 160	100 - 250

Characteristics Curve

